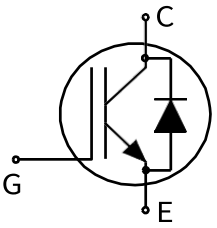
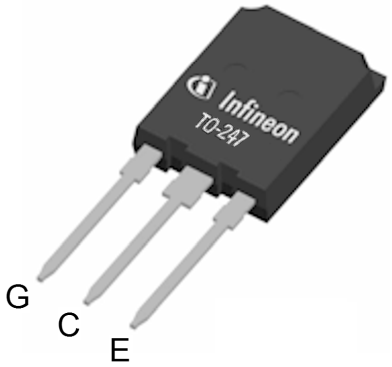
英飞凌 TRENCHSTOP™2 低$V_{ce(sat)}$第二代IGBT

采用 TRENCHSTOP™ 2 技术的IGBT低 $V_{ce(sat)}$与软、快速恢复、全电流额定反并联发射极控制二极管共同封装



特性：

TRENCHSTOP™ 2 技术提供：
- 非常低的 $V_{CE(sat)}$，标称电流时为 1.75V
- T_{vj} =175°C 时短路耐受时间为 10µsec
- 由于 $V_{CE(sat)}$具有正温度系数，因此易于并联
- 低电磁干扰
- 非常软、快速恢复的全电流反并联二极管
- 最高结温 175°C
- 无铅镀层；符合RoHS标准
- 完整的产品系列和 PSpice 模型：
http://www.infineon.com/igbt



应用：

- GPD（通用驱动器）
- 伺服驱动器
- 商用车
- 农用车辆
- 三电平组串太阳能逆变器
- 焊接

产品验证：

符合JEDEC47/20/22相关测试的工业应用要求

关键性能和封装参数

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
IKQ75N120CT2	1200V	75A	1.75V	175°C	K75MCT2	PG-TO247-3-46

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 infineon.com 参考最新的英文版本（控制文档）。

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TRENCHSTOP™2 低$V_{ce(sat)}$第二代IGBT

最大额定值

注意：为了获得最佳的使用寿命和可靠性，英飞凌建议运行条件不超过本数据手册中所述最大额定值的 80%。

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25°C$	V_{CE}	1200	V
DC collector current, limited by T_{vjmax} T_c = 25°C value limited by bondwire T_c = 137°C	I_C	150.0 75.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	300.0	A
Turn off safe operating area $V_{CE} \leq 1200V$, $T_{vj} \leq 175°C$, $t_p = 1µs$	-	300.0	A
Diode forward current, limited by T_{vjmax} T_c = 25°C value limited by bondwire T_c = 100°C	I_F	150.0 75.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	300.0	A
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time V_{GE} = 15.0V, $V_{CC} \leq 600V$ Allowed number of short circuits < 1000 Time between short circuits: ≥ 1.0s T_{vj} = 175°C	t_{SC}	10	µs
Power dissipation T_c = 25°C Power dissipation T_c = 137°C	P_{tot}	938.0 237.0	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

热阻抗

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R_{th} 特性						
IGBT thermal resistance,[1] junction - case	$R_{th(j-c)}$		-	-	0.16	K/W
Diode thermal resistance,[1] junction - case	$R_{th(j-c)}$		-	-	0.28	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

[1]热阻抗$R_{th(c-s)}$（外壳到散热器）大于0.1K/W的导热硅脂不包括在内。

电气特性，测于 T_{vj}= 25°C 的条件下，除非另有规定

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
静态特性						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 0.50mA	1200	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	V_{GE} = 15.0V, I_C = 75.0A T_{vj} = 25°C T_{vj} = 175°C	- -	1.75 2.30	2.15 -	V
Diode forward voltage	V_F	V_{GE} = 0V, I_F = 75.0A T_{vj} = 25°C T_{vj} = 175°C	- -	1.90 1.85	2.30 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 2.60mA, V_{CE} = V_{GE}	5.1	5.8	6.5	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 1200V, V_{GE} = 0V T_{vj} = 25°C T_{vj} = 150°C T_{vj} = 175°C	- -	- - 5000	450 - -	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE} = 20V, I_C = 75.0A	-	27.0	-	S

电气特性，测于 T_{vj} = 25°C的条件下，除非另有规定

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
动态特性						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	4856	-	pF
Output capacitance	C_{oes}		-	505	-	
Reverse transfer capacitance	C_{res}		-	290	-	
Gate charge	Q_G	V_{CC} = 960V, I_C = 75.0A, V_{GE} = 15V	-	370.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH

开关特性、感性负载

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT 特性，测于T_{vj} = 25°C的条件下						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 600V, I_C = 75.0A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 6.0Ω, $R_{G(off)}$ = 6.0Ω, Lσ = 90nH, Cσ = 67pF Lσ, Cσ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	37	-	ns
Rise time	t_r		-	49	-	ns
Turn-off delay time	$t_{d(off)}$		-	326	-	ns
Fall time	t_f		-	46	-	ns
Turn-on energy	E_{on}		-	6.70	-	mJ
Turn-off energy	E_{off}		-	4.10	-	mJ
Total switching energy	E_{ts}		-	10.80	-	mJ

二极管特性， T_{vj} = 25°C

Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 600V, I_F = 75.0A, di_F/dt = 800A/µs	-	320	-	ns
Diode reverse recovery charge	Q_{rr}		-	5.10	-	µC
Diode peak reverse recovery current	I_{rrm}		-	29.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-300	-	A/µs

开关特性、感性负载

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT 特性，测于 T_{vj} = 175°C的条件						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 175°C, V_{CC} = 600V, I_C = 75.0A, V_{GE} = 0.0/15.0V, $R_{G(on)}$ = 6.0Ω, $R_{G(off)}$ = 6.0Ω, Lσ = 90nH, Cσ = 67pF Lσ, Cσ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	35	-	ns
Rise time	t_r		-	50	-	ns
Turn-off delay time	$t_{d(off)}$		-	460	-	ns
Fall time	t_f		-	103	-	ns
Turn-on energy	E_{on}		-	10.30	-	mJ
Turn-off energy	E_{off}		-	9.10	-	mJ
Total switching energy	E_{ts}		-	19.40	-	mJ

二极管特性，测于 T_{vj} = 175°C的条件下

Diode reverse recovery time	t_{rr}	T_{vj} = 175°C, V_R = 600V, I_F = 75.0A, di_F/dt = 800A/µs	-	600	-	ns
Diode reverse recovery charge	Q_{rr}		-	13.30	-	µC
Diode peak reverse recovery current	I_{rrm}		-	42.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-125	-	A/µs

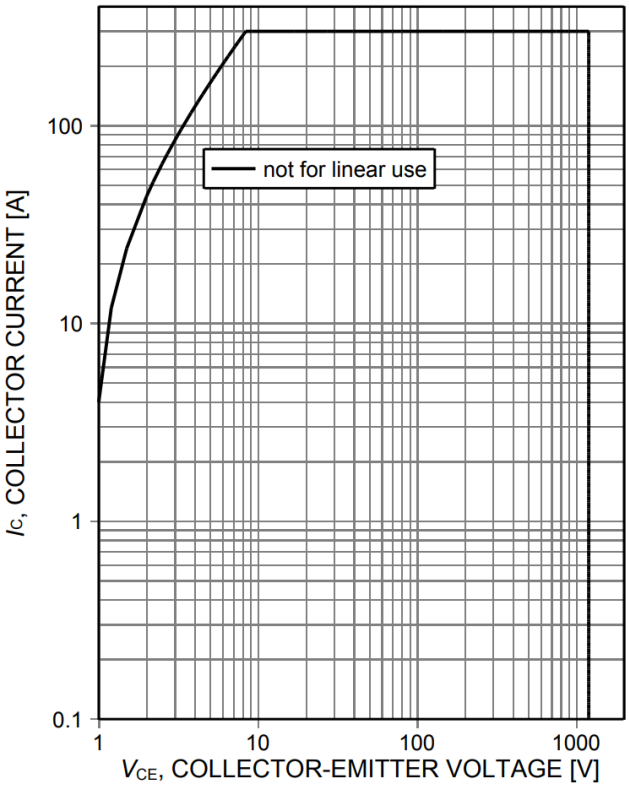


Figure 1. **Forward bias safe operating area**
(D=0, T_C=25°C, T_{vj}≤175°C; V_{GE}=15V)

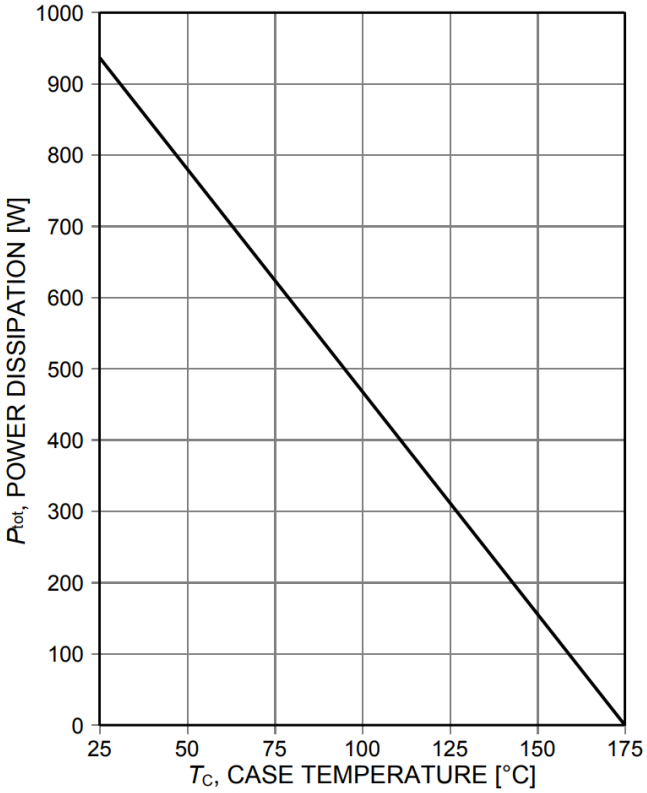


Figure 2. **Power dissipation as a function of case temperature**
(T_{vj}≤175°C)

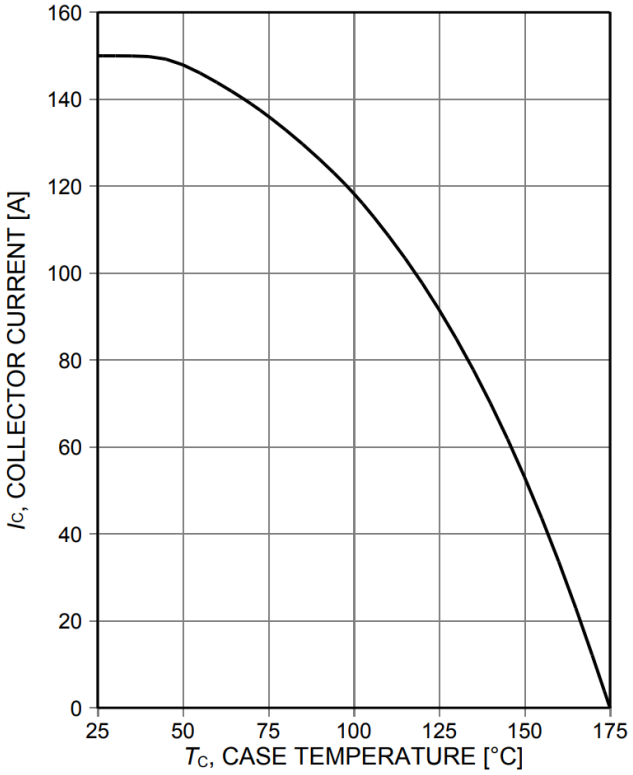


Figure 3. **Collector current as a function of case temperature**
(V_{GE}≥15V, T_{vj}≤175°C)

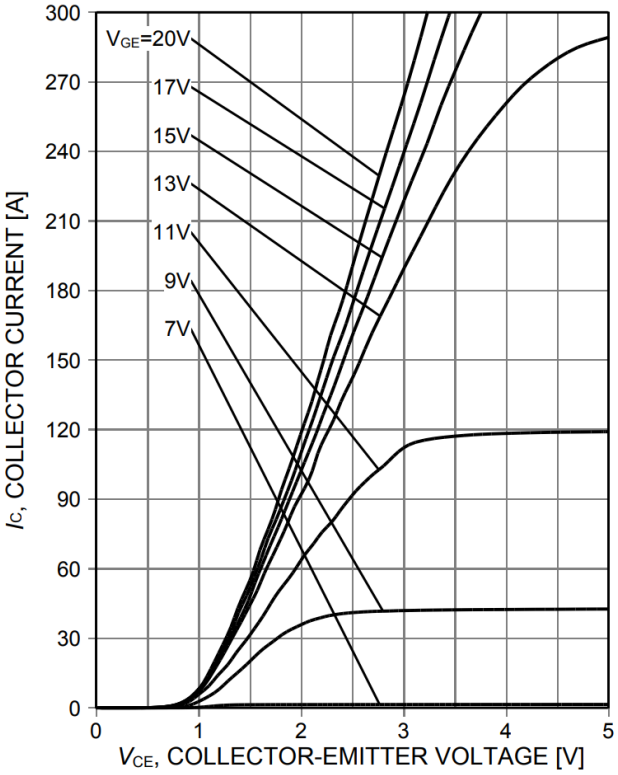


Figure 4. **Typical output characteristic**
(T_{vj}=25°C)

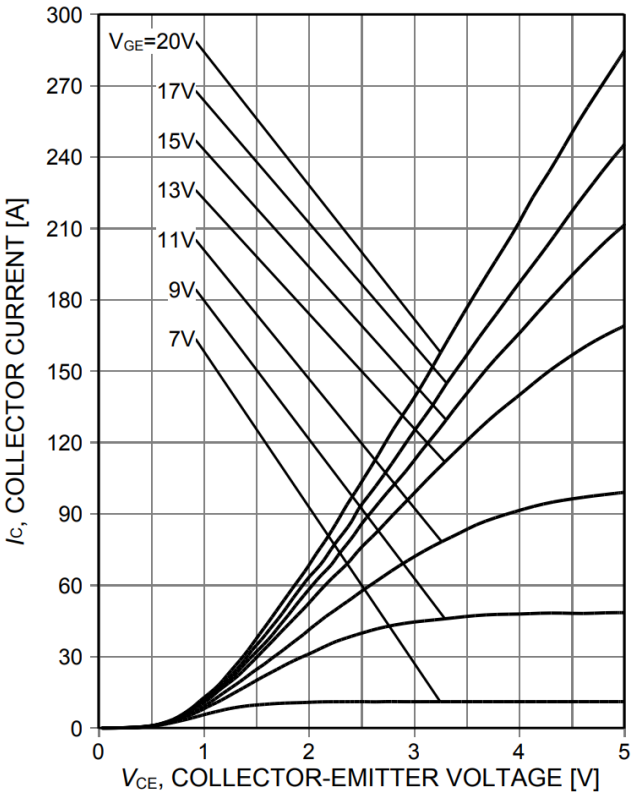


Figure 5. **Typical output characteristic** (T_{vj}=175°C)

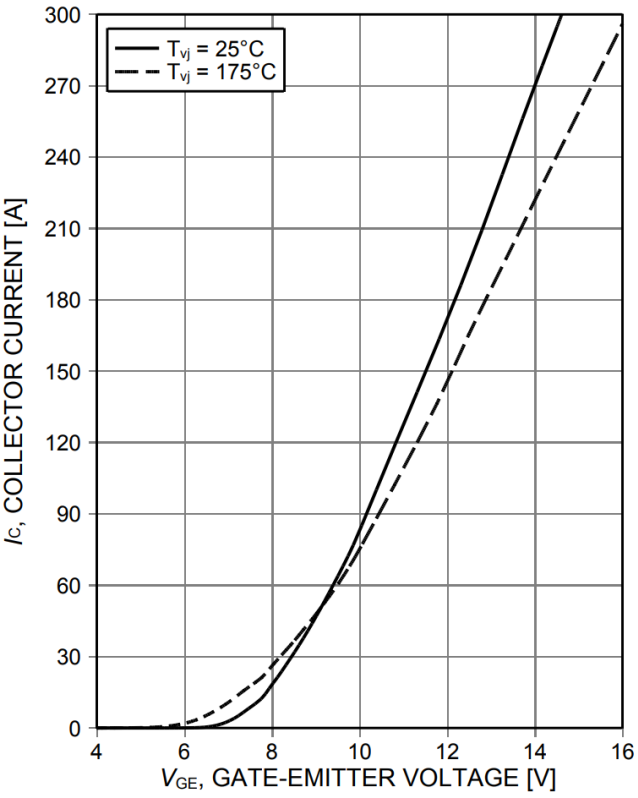


Figure 6. **Typical transfer characteristic** (V_{CE}=20V)

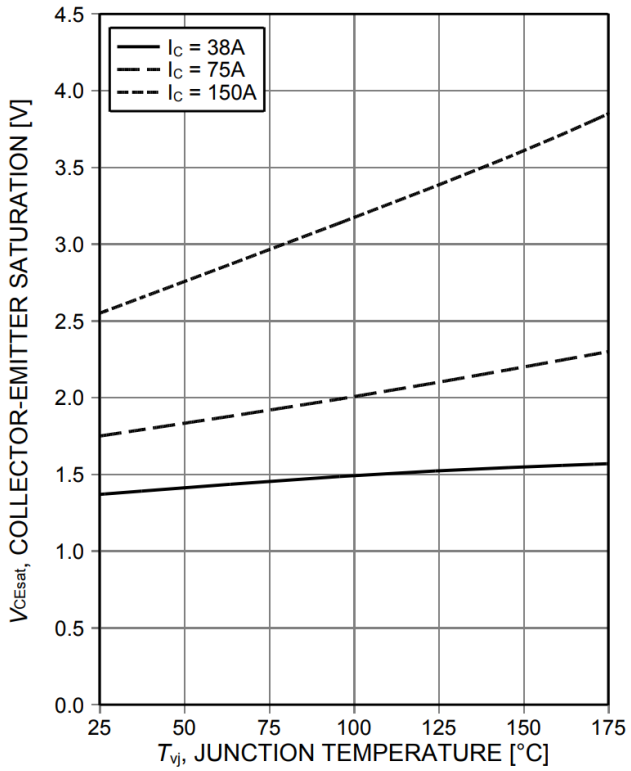


Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature** (V_{GE}=15V)

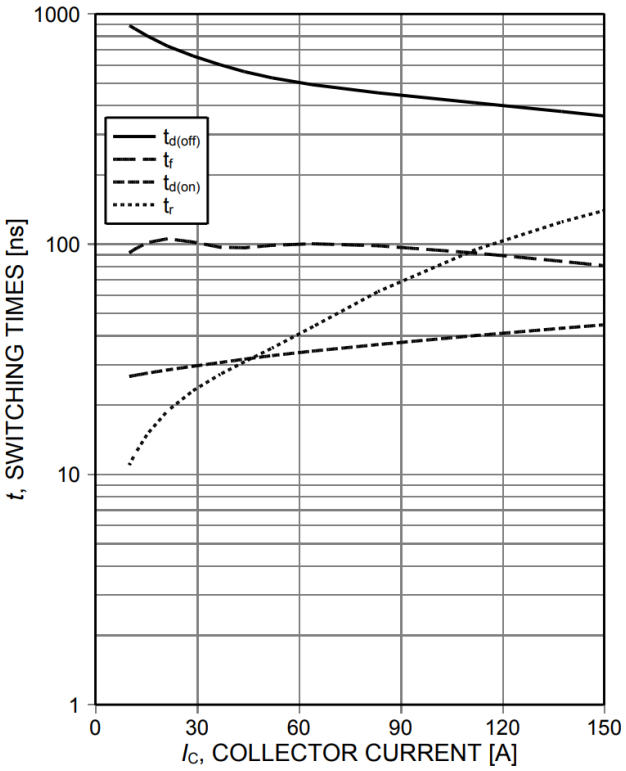


Figure 8. **Typical switching times as a function of collector current** (inductive load, T_{vj}=175°C, V_{CE}=600V, V_{GE}=0/15V, r_G=6Ω, Dynamic test circuit in Figure E)

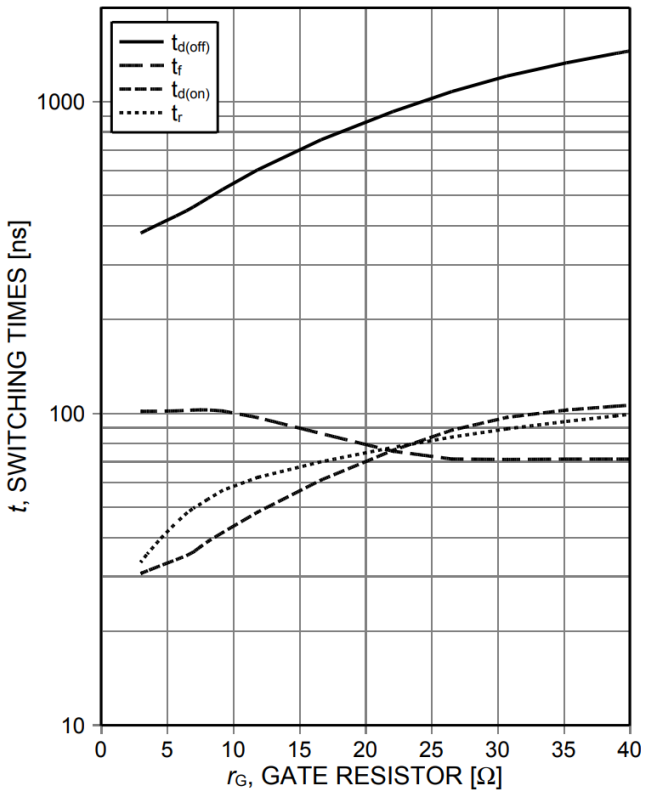


Figure 9. **Typical switching times as a function of gate resistor**
(inductive load, T_{vj}=175°C, V_{CE}=600V, V_{GE}=0/15V, I_C=75A, Dynamic test circuit in Figure E)

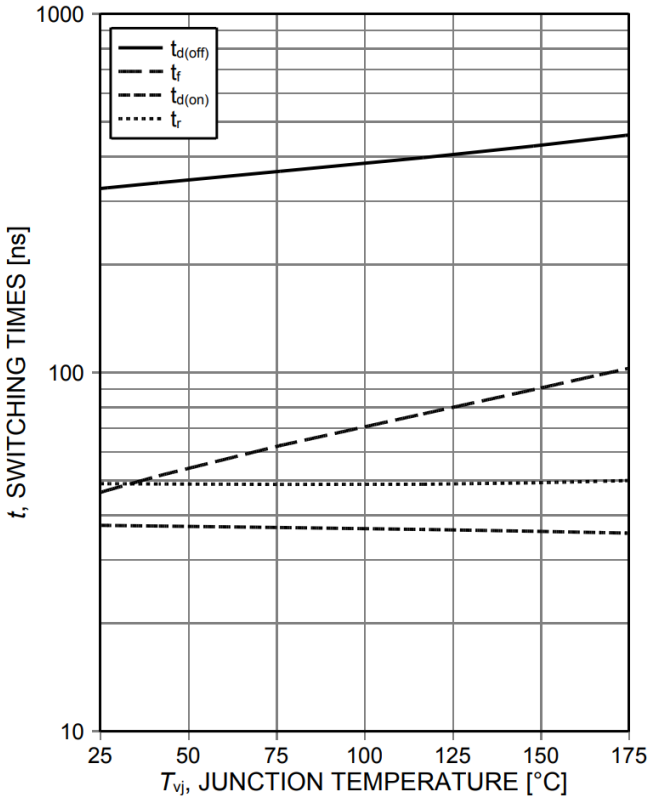


Figure 10. **Typical switching times as a function of junction temperature**
(inductive load, V_{CE}=600V, V_{GE}=0/15V, I_C=75A, r_G=6Ω, Dynamic test circuit in Figure E)

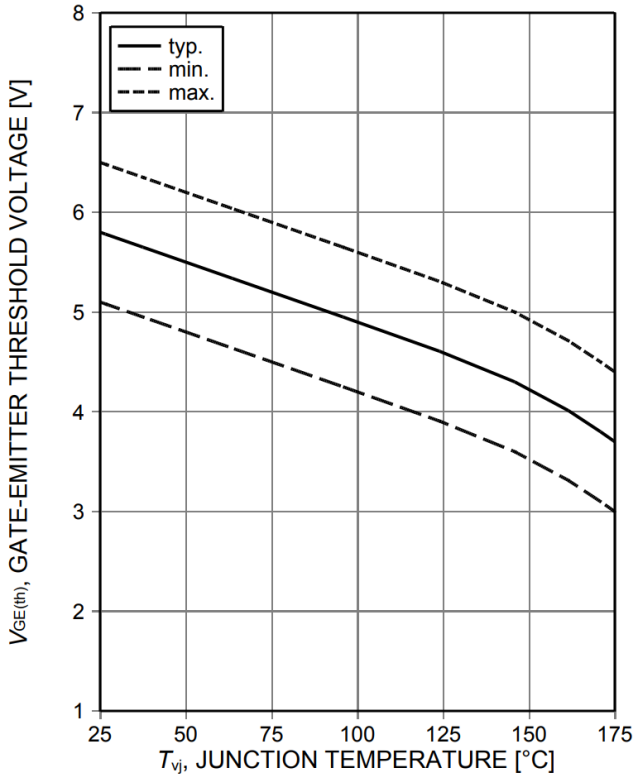


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**
(I_C=2.6mA)

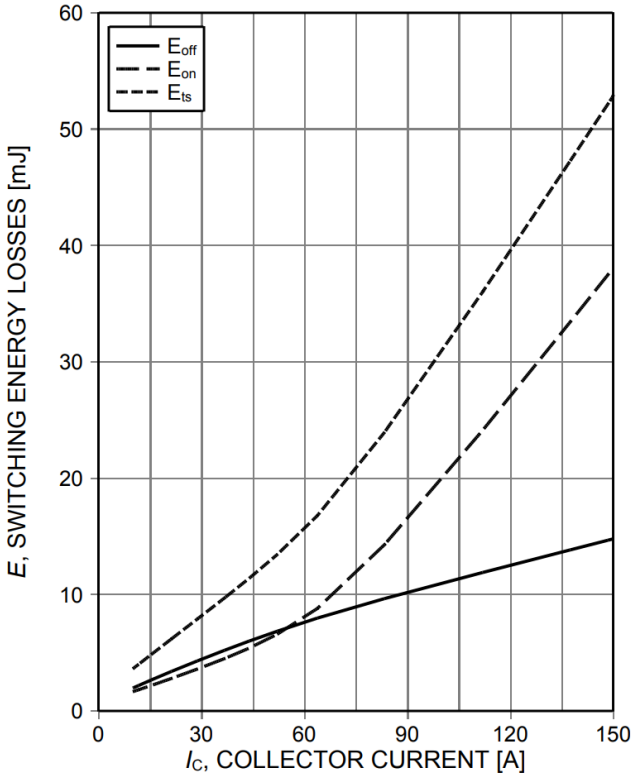


Figure 12. **Typical switching energy losses as a function of collector current**
(inductive load, T_{vj}=175°C, V_{CE}=600V, V_{GE}=0/15V, r_G=6Ω, Dynamic test circuit in Figure E)

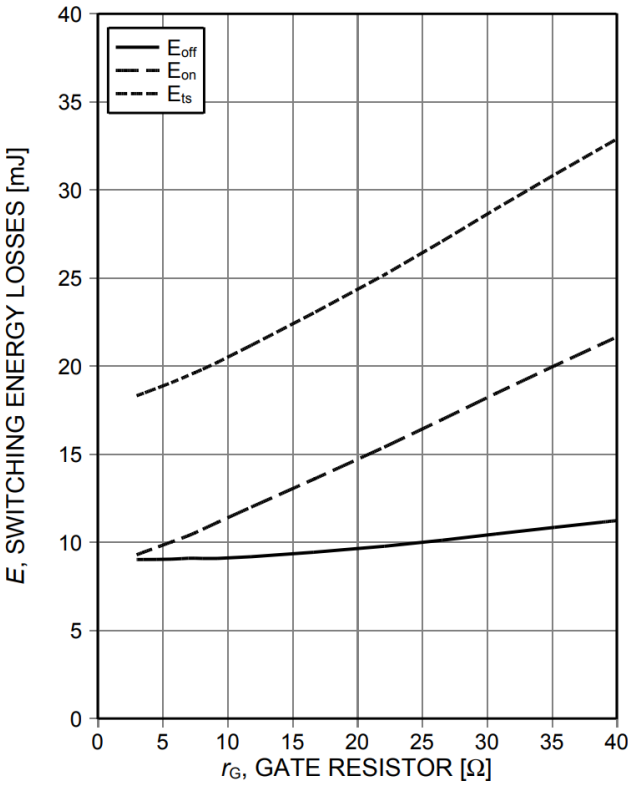


Figure 13. **Typical switching energy losses as a function of gate resistor**
(inductive load, T_{vj}=175°C, V_{CE}=600V, V_{GE}=0/15V, I_C=75A, Dynamic test circuit in Figure E)

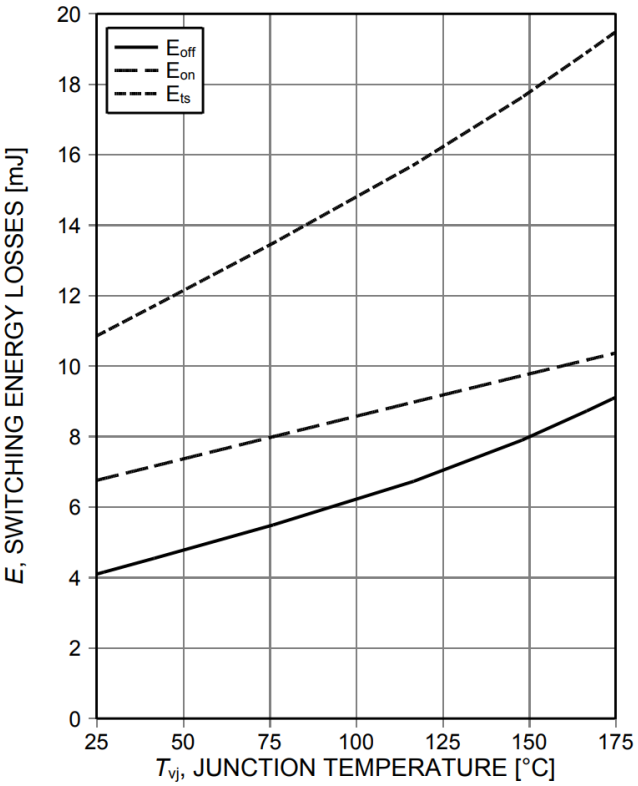


Figure 14. **Typical switching energy losses as a function of junction temperature**
(inductive load, V_{CE}=600V, V_{GE}=0/15V, I_C=75A, r_G=6Ω, Dynamic test circuit in Figure E)

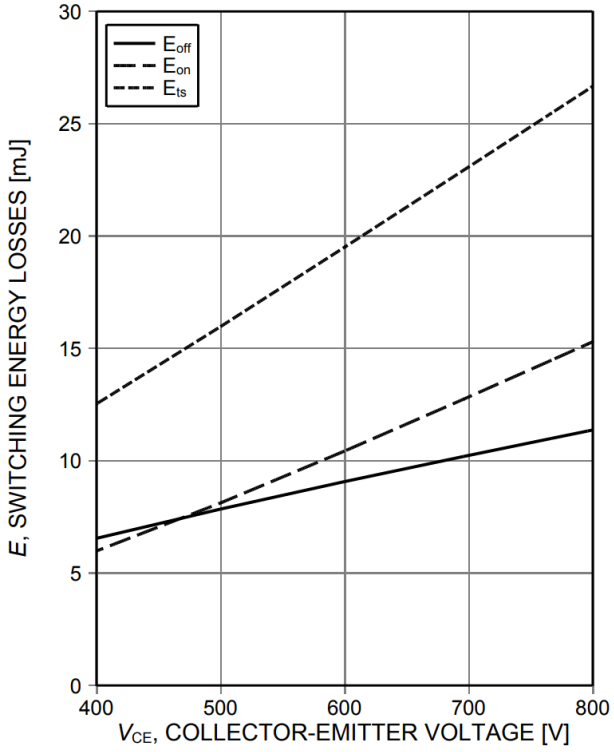


Figure 15. **Typical switching energy losses as a function of collector emitter voltage**
(inductive load, T_{vj}=175°C, V_{GE}=0/15V, I_C=75A, r_G=6Ω, Dynamic test circuit in Figure E)

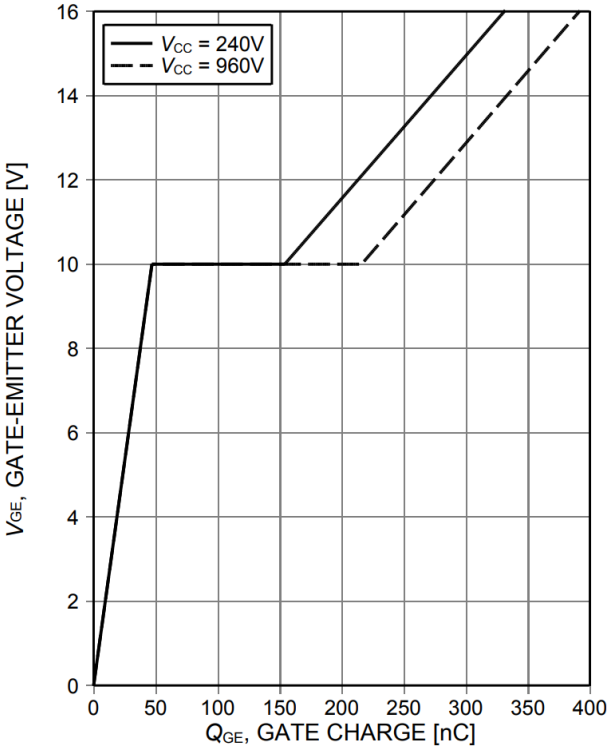


Figure 16. **Typical gate charge**
(I_C=75A)

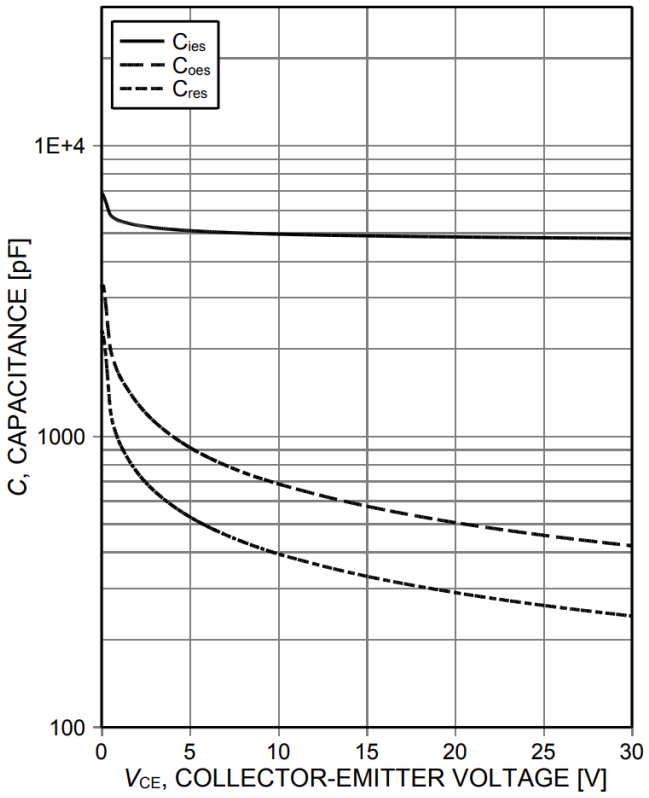


Figure 17. **Typical capacitance as a function of collector-emitter voltage**
(V_{GE}=0V, f=1MHz)

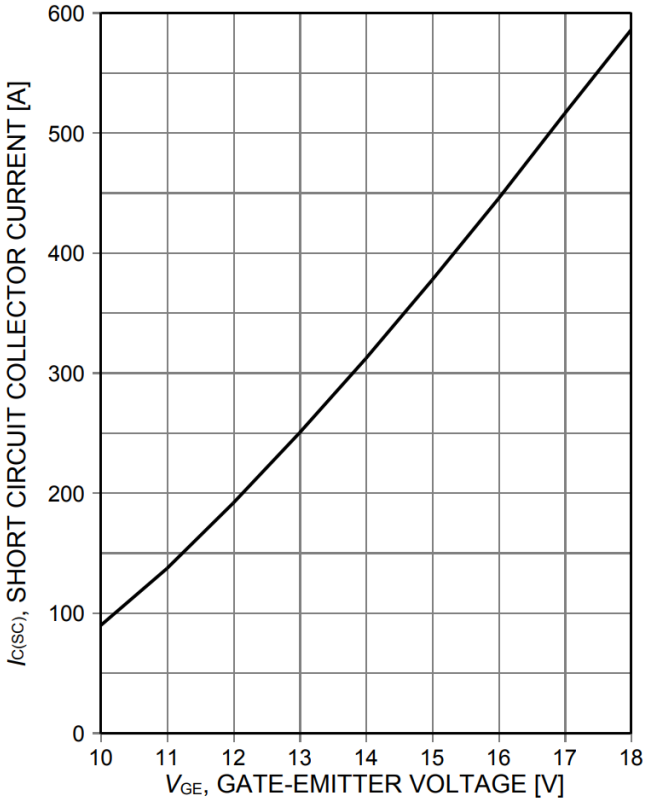


Figure 18. **Typical short circuit collector current as a function of gate-emitter voltage**
(V_{CE}≤600V, T_{vj}≤175°C)

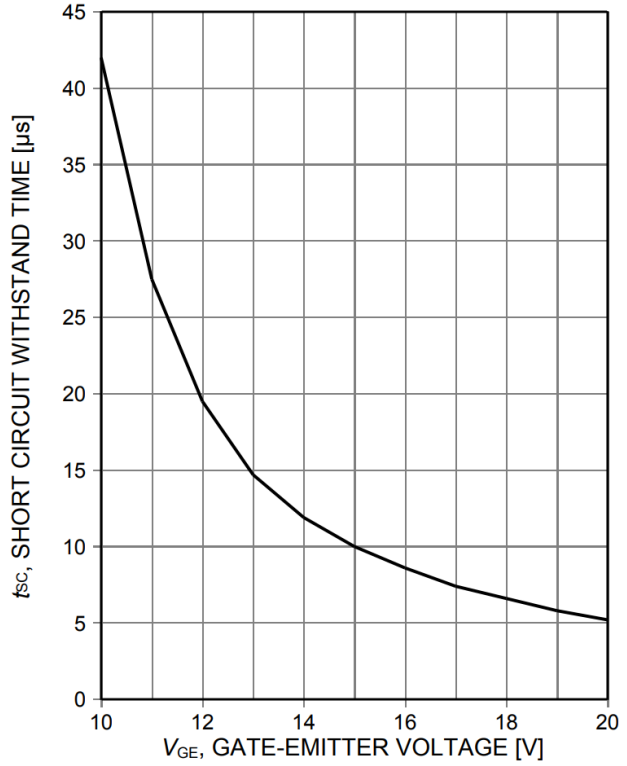


Figure 19. **Short circuit withstand time as a function of gate-emitter voltage**
(V_{CE}≤600V, start at T_{vj}≤175°C)

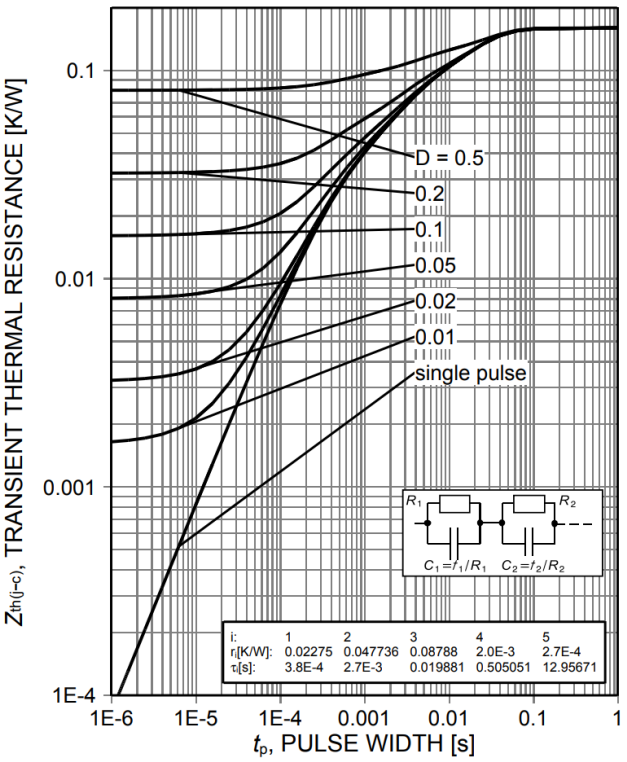


Figure 20. **IGBT transient thermal resistance**
($D=t_p/T$)

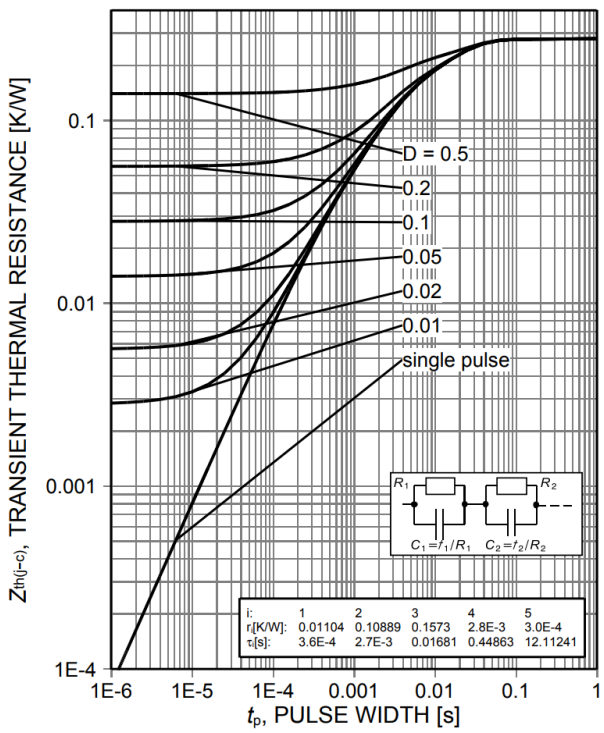


Figure 21. **Diode transient thermal impedance as a function of pulse width**
($D=t_p/T$)

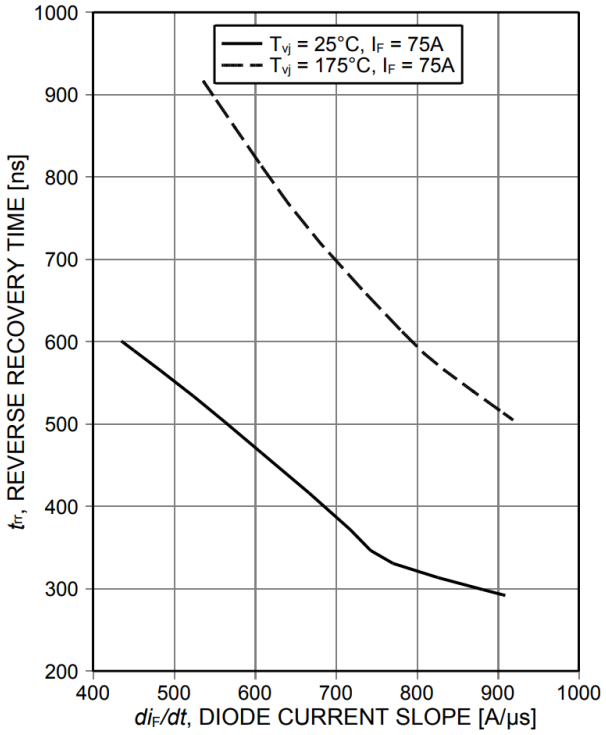


Figure 22. **Typical reverse recovery time as a function of diode current slope**
(V_R=600V)

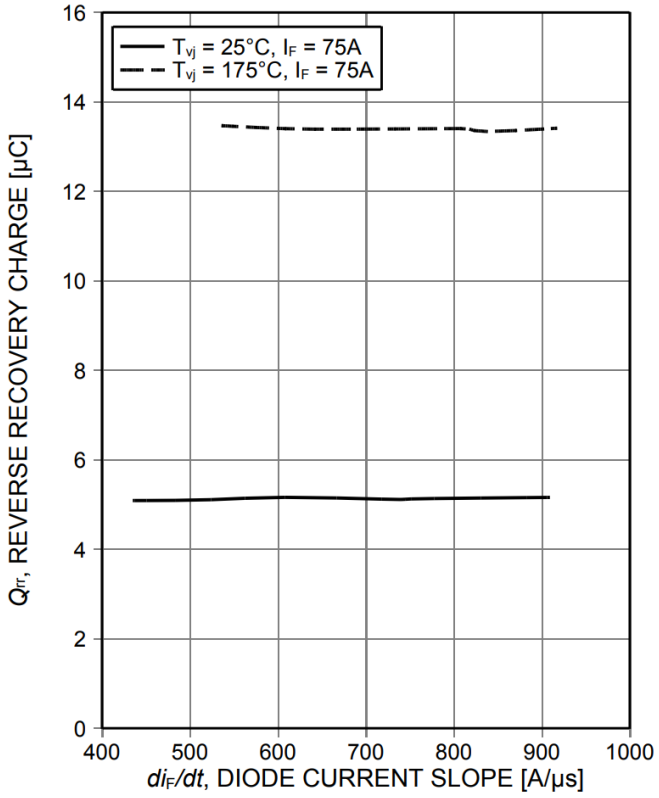


Figure 23. **Typical reverse recovery charge as a function of diode current slope**
(V_R=600V)

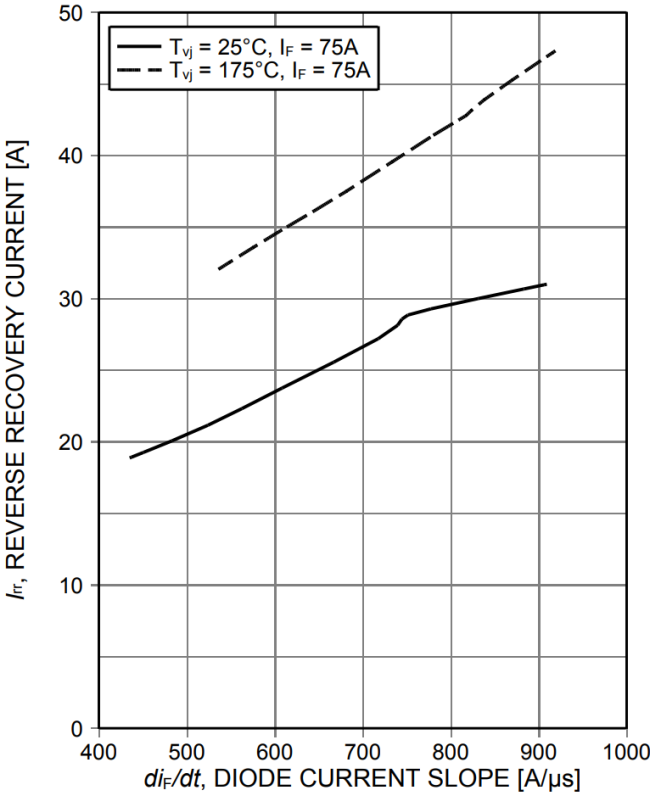


Figure 24. **Typical reverse recovery current as a function of diode current slope**
(V_R=600V)

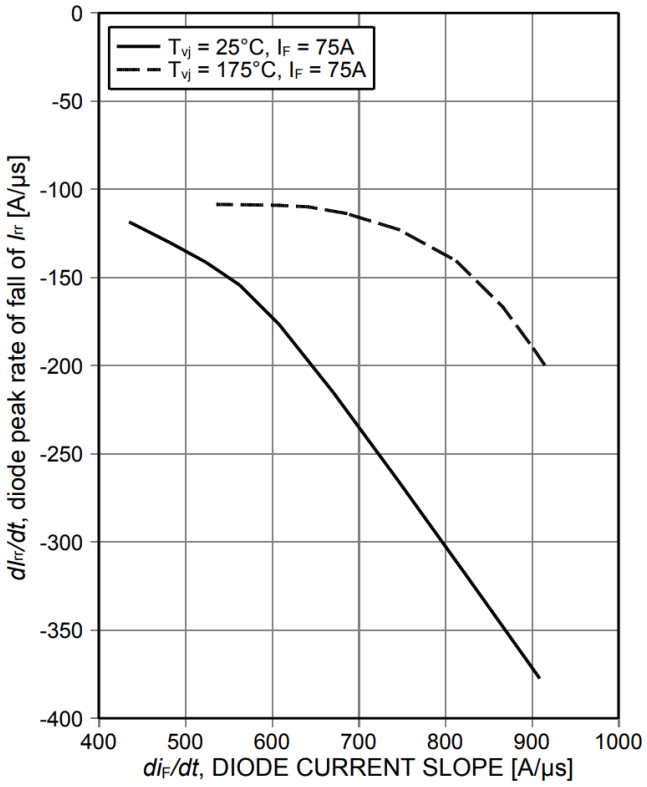


Figure 25. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
(V_R=600V)

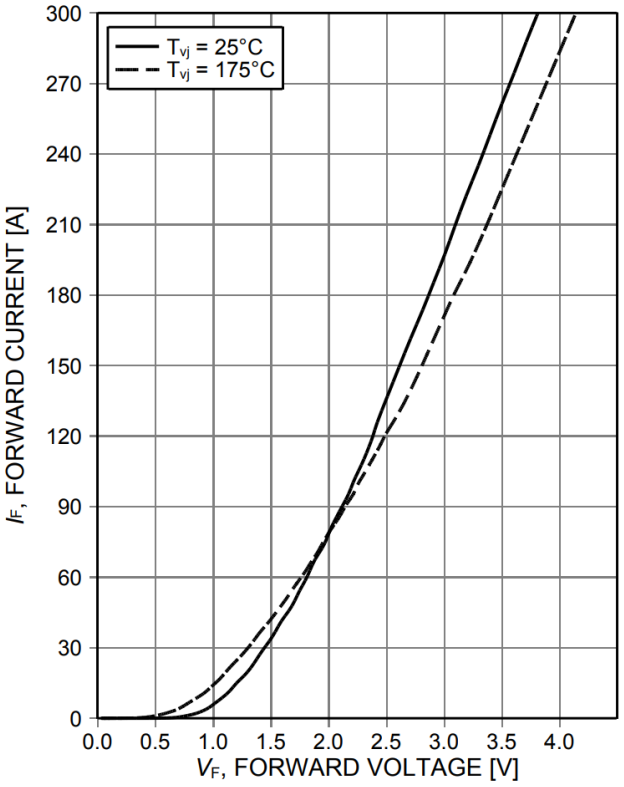


Figure 26. **Typical diode forward current as a function of forward voltage**

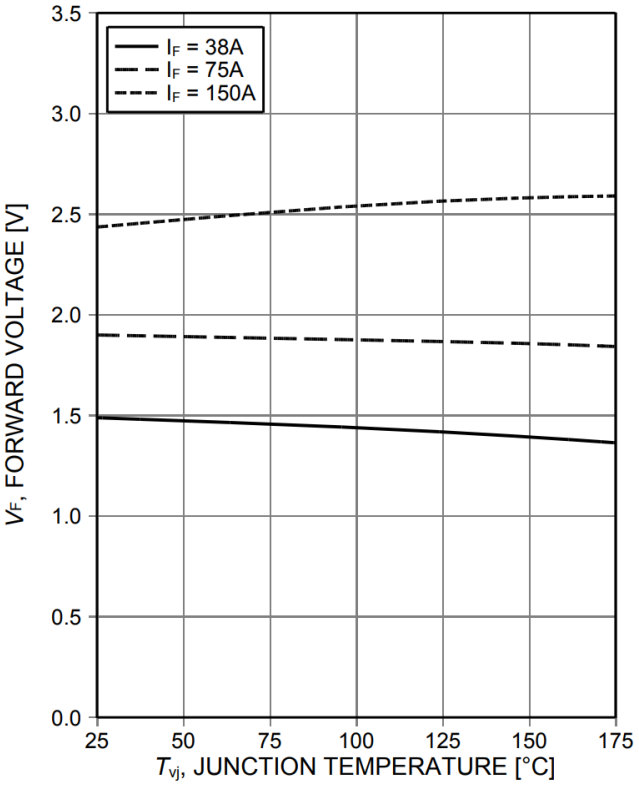
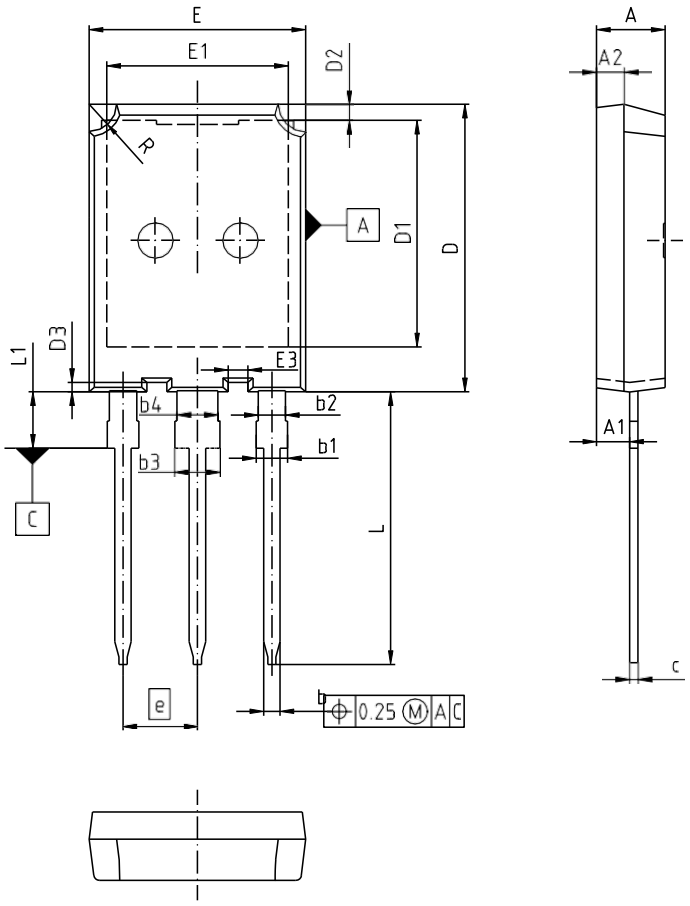


Figure 27. **Typical diode forward voltage as a function of junction temperature**

PG-TO247-3-46 封装图



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.96	2.25	0.077	0.089
b2	1.96	2.06	0.077	0.081
c	0.59	0.66	0.023	0.026
D	20.90	21.10	0.823	0.831
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
D3	0.58	0.78	0.023	0.031
E	15.70	15.90	0.618	0.626
E1	13.10	13.50	0.516	0.531
E3	1.35	1.55	0.053	0.061
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.10	0.780	0.791
L1	-	4.30	-	0.169
R	1.90	2.10	0.075	0.083

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EUROPEAN PROJECTION	
ISSUE DATE	13-08-2014
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测试条件

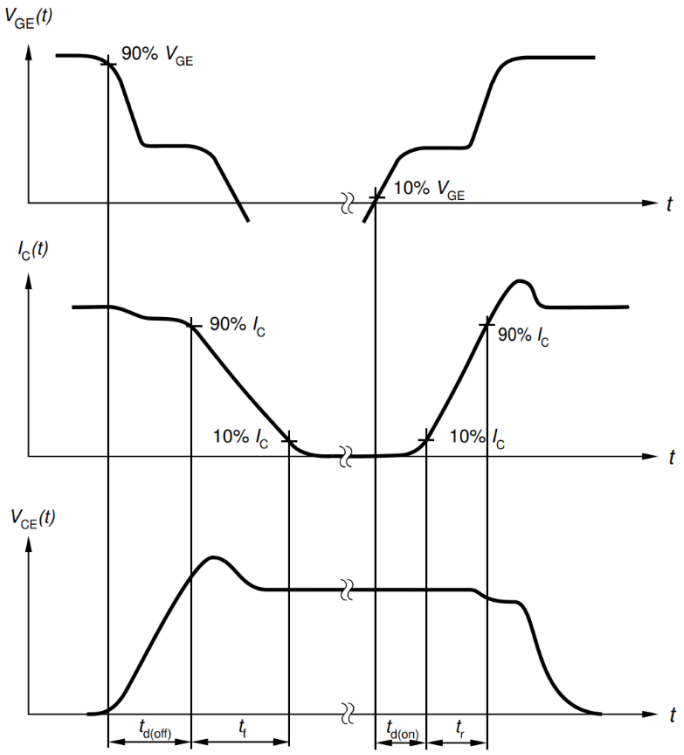

Figure A. **Definition of switching times**

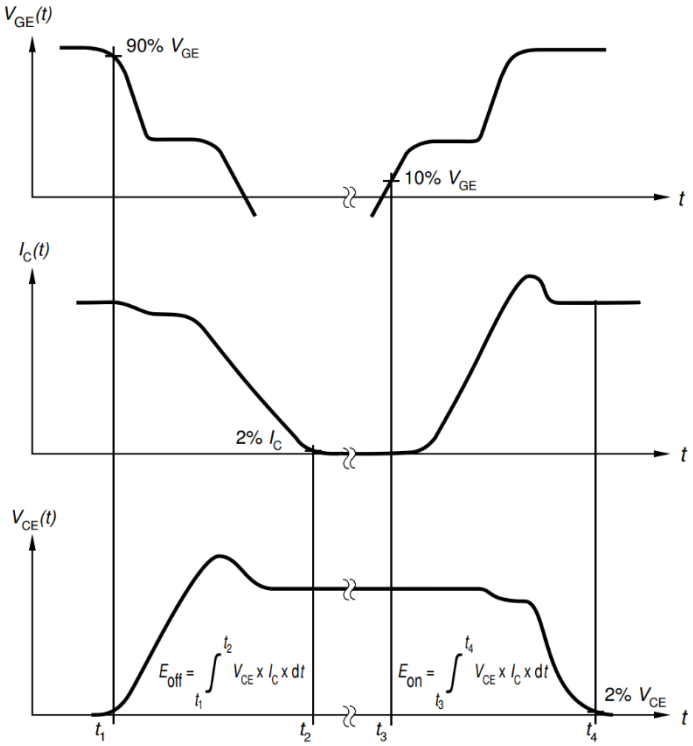

Figure B. **Definition of switching losses**

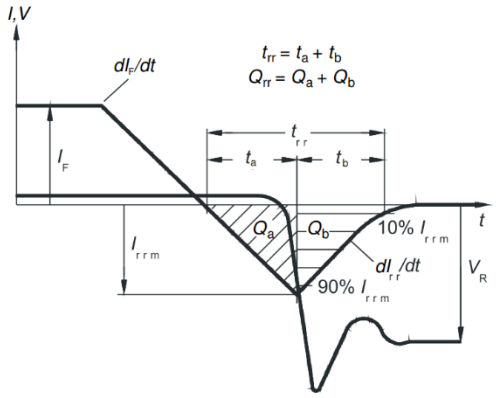

Figure C. **Definition of diode switching characteristics**

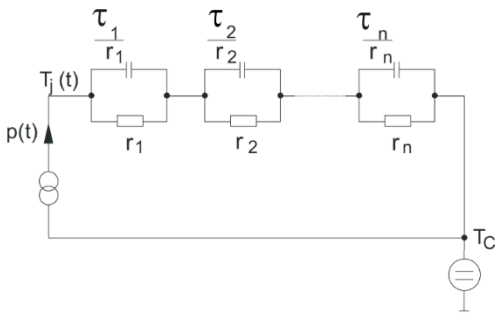

Figure D. **Thermal equivalent circuit**

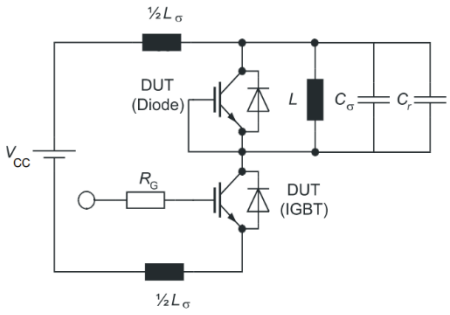

Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

开关特性的定

TRENCHSTOP™2 低$V_{ce(sat)}$第二代IGBT

修订记录

IKQ75N120CT2

Revision: 2019-04-15, Rev. 2.3

历史修订版本

Revision	Date	Subjects (major changes since last revision)
2.1	2017-04-26	Final data sheet
2.2	2017-05-02	Update figure 7
2.3	2019-04-15	Update condition for Vgeth page 4 and Fig. 11

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